



3CD6

PNP Silicon Low Frequency High Power Transistor



Features:

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications								Test Condition
			A	B	C	D	E	F	G	H	
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150	200	250	300	
Emitter-Base Voltage	V_{EBO}	V	4								
Max. Collector Current	I_{CM}	A	5								
Max. Collector Dissipation	P_{CM}	W	50								($T_c:75^\circ\text{C}$)
Junction Temperature	T_{jm}	$^\circ\text{C}$	175								
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175								
Collector-Emitter Leakage Current	I_{CEO}	mA	2								$V_{CE}=20\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5								A~E: $I_C=2.5\text{A}$, $I_B=0.5\text{A}$
											F~H: $I_C=1.0\text{A}$, $I_B=0.2\text{A}$
DC Current Gain	h_{FE}		Max.:240				Min.:15				A~E: $V_{CE}=10\text{V}$, $I_C=2.5\text{A}$
											F~H: $V_{CE}=10\text{V}$, $I_C=1.0\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	F	G	H	$I_C=5\text{mA}$
			30	50	80	110	150	200	250	300	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	4								$I_E=3\text{mA}$

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~240

Outline and Dimensions: